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Team Nexperia

PMZB300XN

20 V, single N-channel Trench MOSFET

1 August 2012

Product data sheet

1. Product profile

1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Fast switching
- Trench MOSFET technology
- Low threshold voltage
- Ultra thin package profile of 0.37mm height

1.3 Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_J = 25\text{ }^{\circ}\text{C}$		-	-	20	V
V_{GS}	gate-source voltage			-12	-	12	V
I_D	drain current	$V_{GS} = 4.5\text{ V}; T_{amb} = 25\text{ }^{\circ}\text{C}$	[1]	-	-	1	A
Static characteristics							
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 4.5\text{ V}; I_D = 200\text{ mA}; T_J = 25\text{ }^{\circ}\text{C}$		-	0.3	0.38	Ω

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

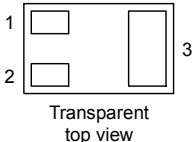
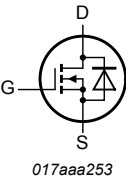


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2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 Transparent top view DFN1006B-3 (SOT883B)	 017aaa253
2	S	source		
3	D	drain		

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMZB300XN	DFN1006B-3	Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B

4. Marking

Table 4. Marking codes

Type number	Marking code
PMZB300XN	0000 0111

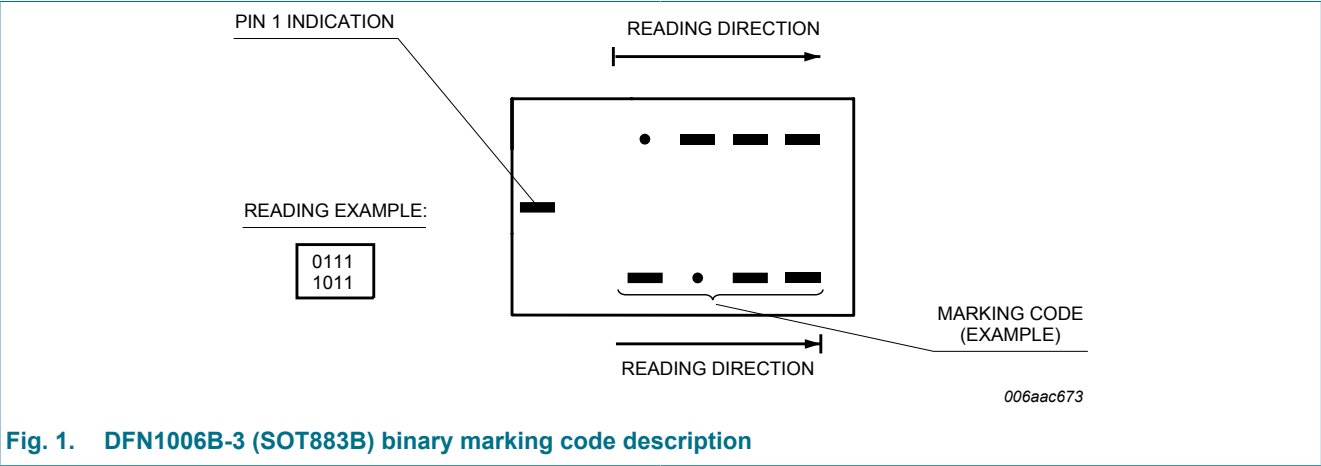


Fig. 1. DFN1006B-3 (SOT883B) binary marking code description

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	20	V
V _{GS}	gate-source voltage			-12	12	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	1	A
		V _{GS} = 4.5 V; T _{amb} = 100 °C	[1]	-	0.6	A
I _{DM}	peak drain current	T _{amb} = 25 °C; single pulse; t _p ≤ 10 μs		-	4	A
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	360	mW
			[1]	-	715	mW
		T _{sp} = 25 °C		-	2700	mW
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain diode						
I _S	source current	T _{amb} = 25 °C	[1]	-	670	mA

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

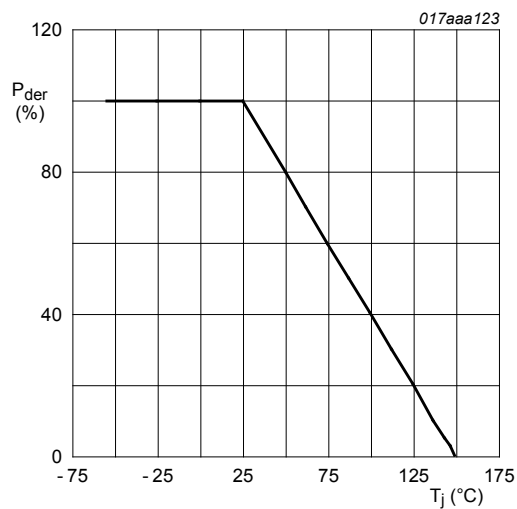


Fig. 2. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}\text{C})}} \times 100 \%$$

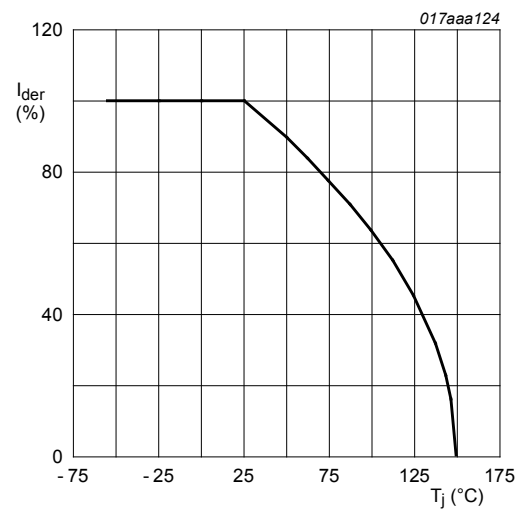
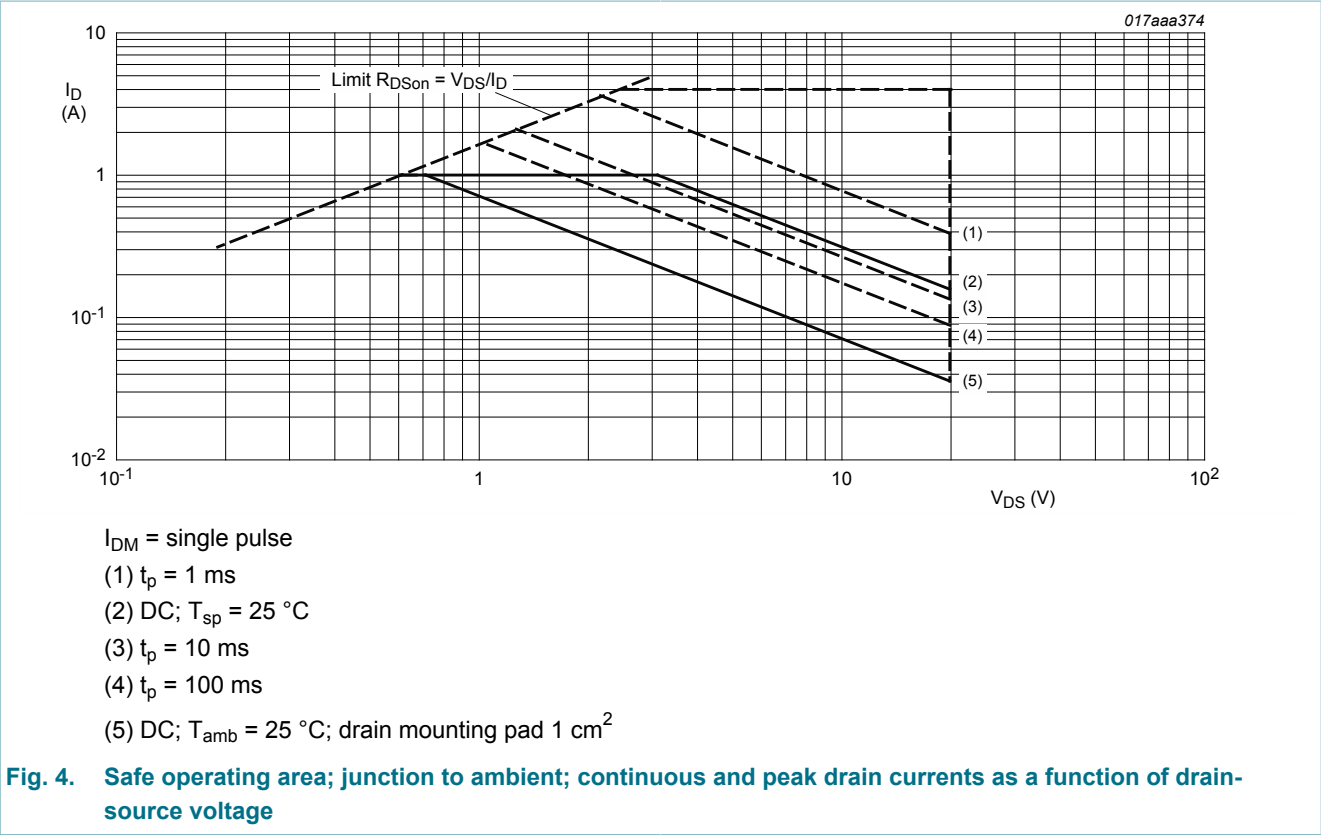


Fig. 3. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100 \%$$



6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	305	360	K/W
			[2]	-	150	175	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	40	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm^2 .

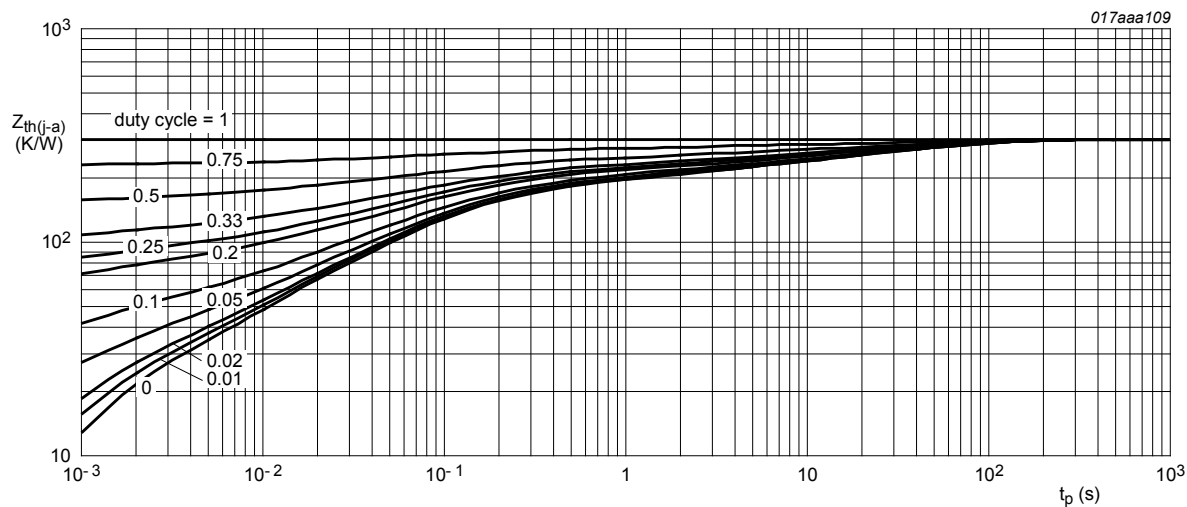


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

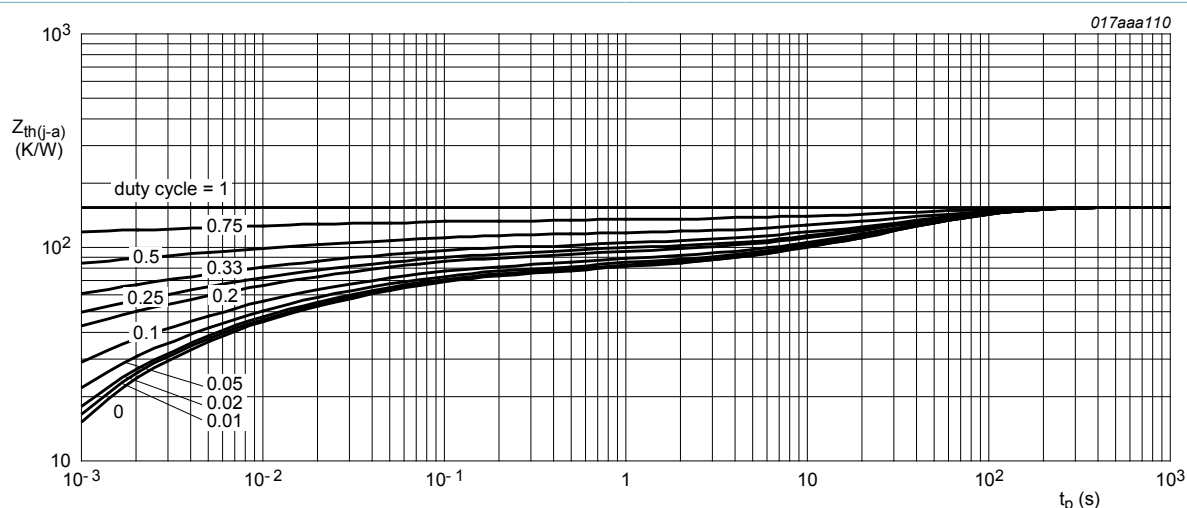


Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 10 \mu A$; $V_{GS} = 0 V$; $T_j = 25^\circ C$	20	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A$; $V_{DS} = V_{GS}$; $T_j = 25^\circ C$	0.5	1	1.5	V
I_{DSS}	drain leakage current	$V_{DS} = 20 V$; $V_{GS} = 0 V$; $T_j = 25^\circ C$	-	-	1	μA
		$V_{DS} = 20 V$; $V_{GS} = 0 V$; $T_j = 150^\circ C$	-	-	100	μA

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
I _{GSS}	gate leakage current	V _{GS} = 12 V; V _{DS} = 0 V; T _j = 25 °C		-	-	0.1	μA
		V _{GS} = -12 V; V _{DS} = 0 V; T _j = 25 °C		-	-	0.1	μA
R _{DSon}	drain-source on-state resistance	V _{GS} = 4.5 V; I _D = 200 mA; T _j = 25 °C		-	0.3	0.38	Ω
		V _{GS} = 4.5 V; I _D = 200 mA; T _j = 150 °C		-	0.54	0.68	Ω
		V _{GS} = 2.5 V; I _D = 100 mA; T _j = 25 °C		-	0.47	0.55	mΩ
g _{fs}	forward transconductance	V _{DS} = 5 V; I _D = 200 mA; T _j = 25 °C		-	1500	-	mS
Dynamic characteristics							
Q _{G(tot)}	total gate charge	V _{DS} = 10 V; I _D = 1 A; V _{GS} = 4.5 V; T _j = 25 °C		-	0.72	0.94	nC
Q _{GS}	gate-source charge			-	0.18	-	nC
Q _{GD}	gate-drain charge			-	0.18	-	nC
C _{iss}	input capacitance	V _{DS} = 20 V; f = 1 MHz; V _{GS} = 0 V; T _j = 25 °C		-	34	51	pF
C _{oss}	output capacitance			-	12	-	pF
C _{rss}	reverse transfer capacitance			-	8	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 10 V; R _L = 10 Ω; V _{GS} = 4.5 V; R _{G(ext)} = 6 Ω; T _j = 25 °C		-	5	10	ns
t _r	rise time			-	11	-	ns
t _{d(off)}	turn-off delay time			-	11	22	ns
t _f	fall time			-	6	-	ns
Source-drain diode							
V _{SD}	source-drain voltage	I _S = 300 mA; V _{GS} = 0 V; T _j = 25 °C		-	0.77	1.2	V

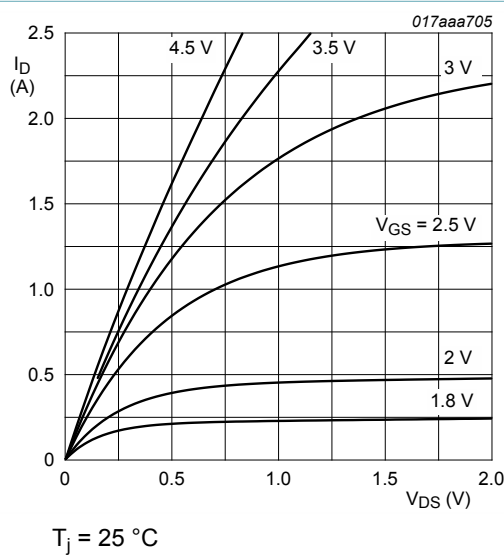


Fig. 7. Output characteristics: drain current as a function of drain-source voltage; typical values

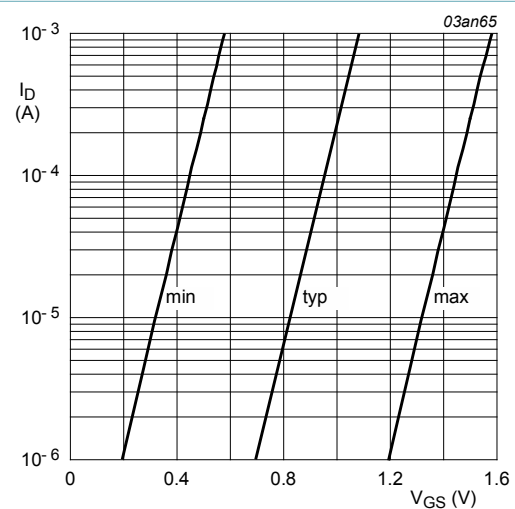


Fig. 8. Subthreshold drain current as a function of gate-source voltage

$T_j = 25\text{ }^{\circ}\text{C}; V_{DS} = 5\text{ V}$

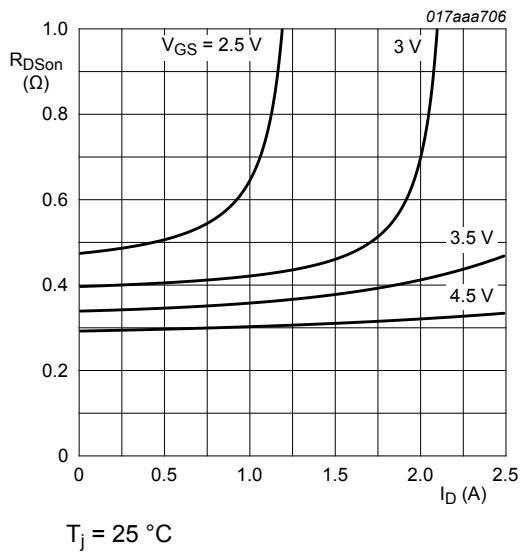


Fig. 9. Drain-source on-state resistance as a function of drain current; typical values

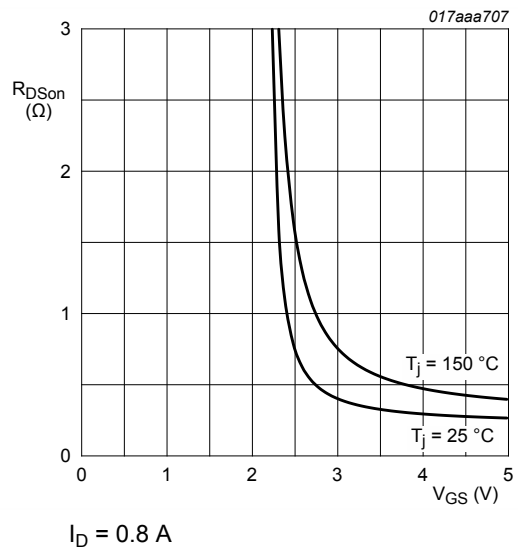


Fig. 10. Drain-source on-state resistance as a function of gate-source voltage; typical values

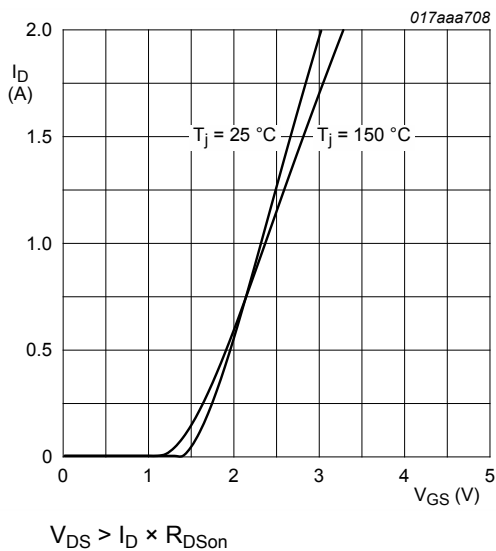


Fig. 11. Transfer characteristics: drain current as a function of gate-source voltage; typical values

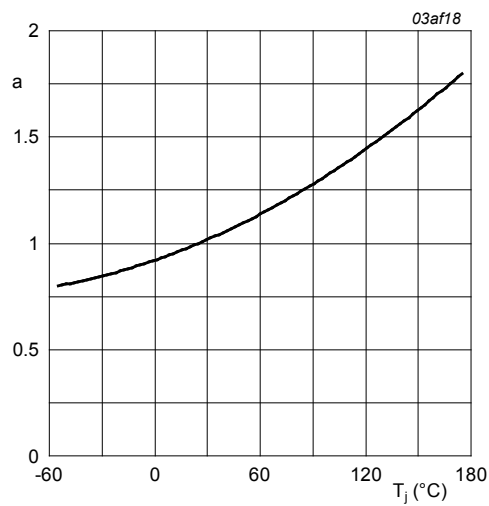


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^\circ C)}}$$

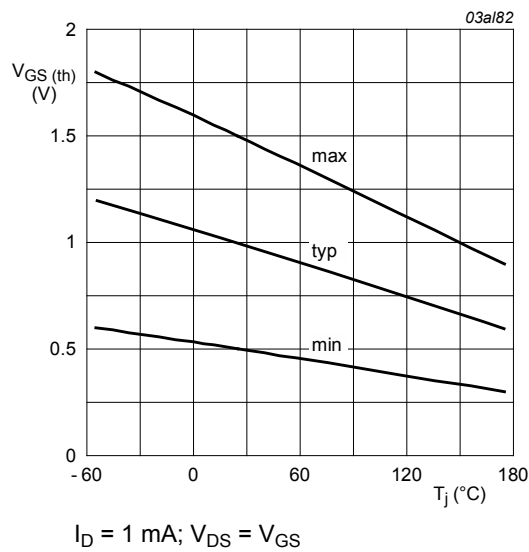


Fig. 13. Gate-source threshold voltage as a function of junction temperature

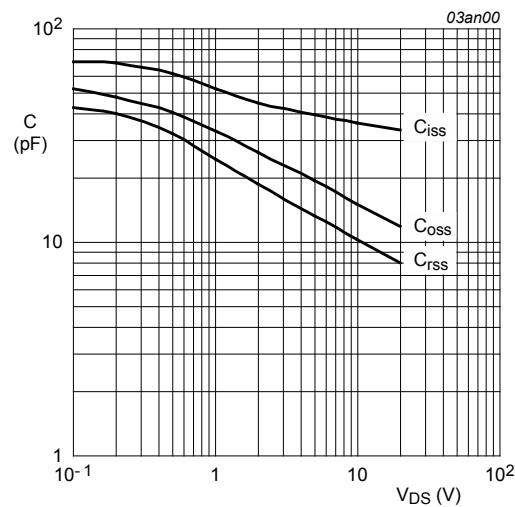


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

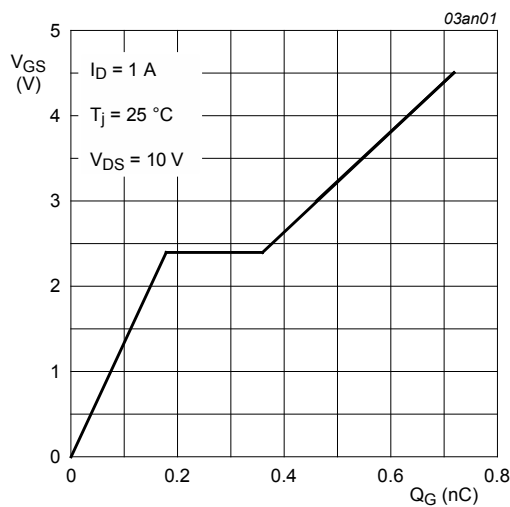


Fig. 15. Gate-source voltage as a function of gate charge; typical values

$I_D = 1\text{ A}; V_{DS} = 10\text{ V}$

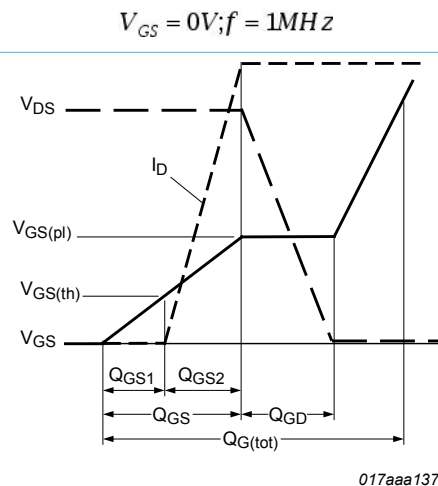
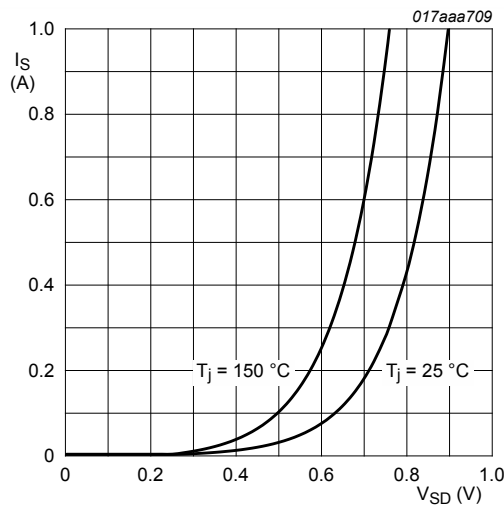


Fig. 16. Gate charge waveform definitions



$V_{GS} = 0\text{ V}$

Fig. 17. Source current as a function of source-drain voltage; typical values

8. Test information

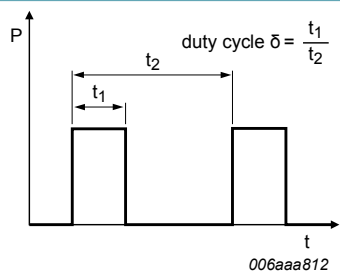


Fig. 18. Duty cycle definition

9. Package outline

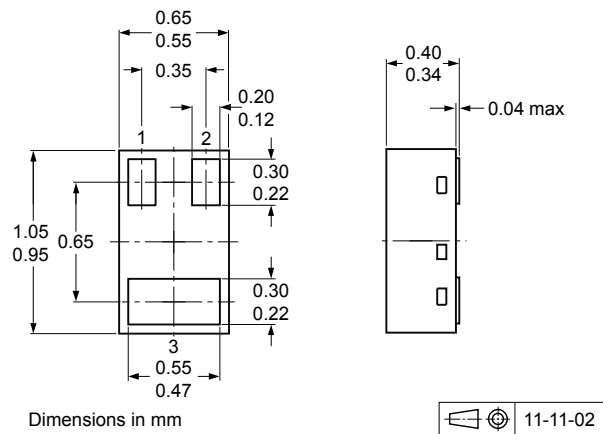
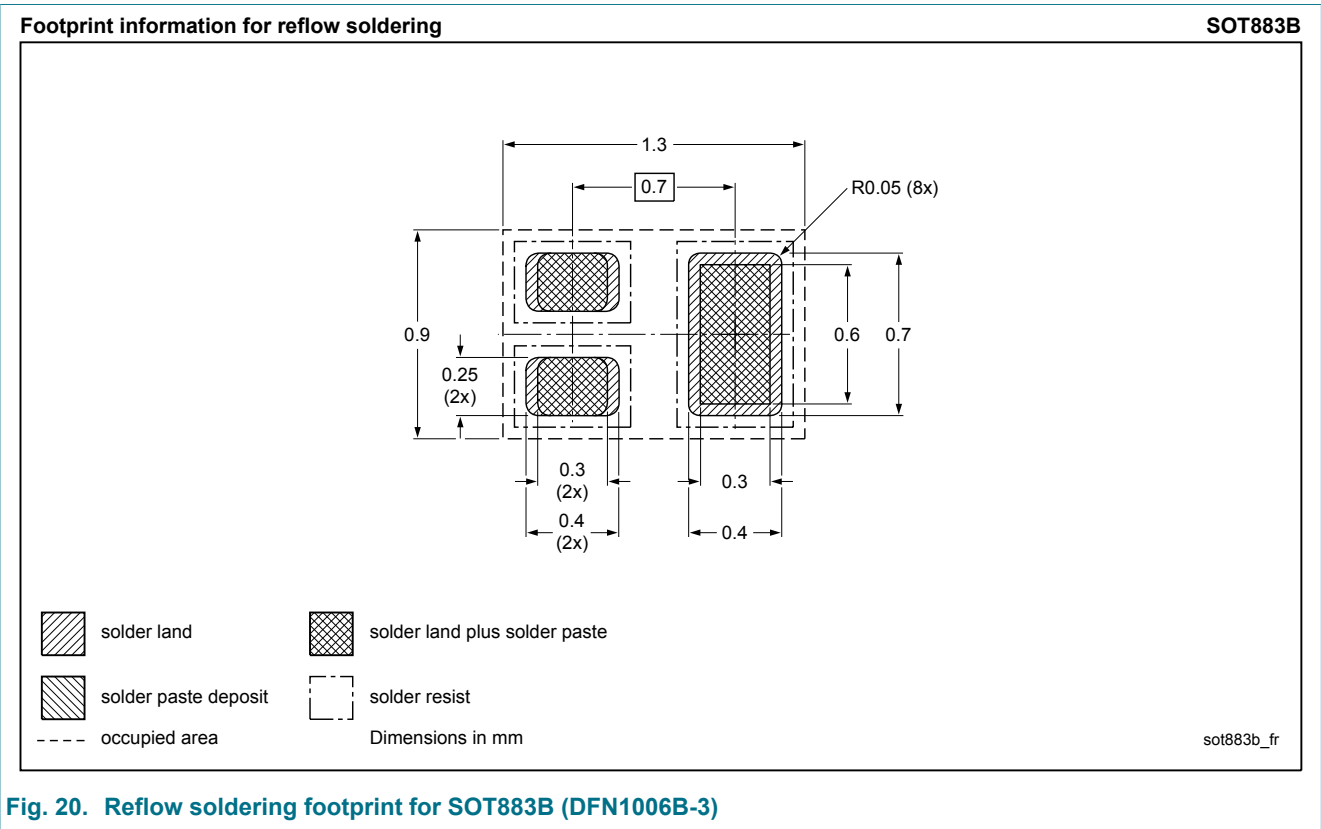


Fig. 19. DFN1006B-3 (SOT883B)

10. Soldering



11. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMZB300XN v.1	20120801	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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13. Contents

1	Product profile	1
1.1	General description	1
1.2	Features and benefits	1
1.3	Applications	1
1.4	Quick reference data	1
2	Pinning information	2
3	Ordering information	2
4	Marking	2
5	Limiting values	3
6	Thermal characteristics	4
7	Characteristics	5
8	Test information	9
9	Package outline	9
10	Soldering	10
11	Revision history	10
12	Legal information	11
12.1	Data sheet status	11
12.2	Definitions	11
12.3	Disclaimers	11
12.4	Trademarks	12

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